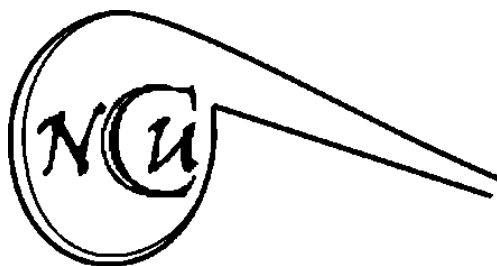


Low thermal conductive chalcogenides for high performance thermoelectric energy conversion



Kanishka Biswas

New Chemistry Unit

Jawaharlal Nehru Centre for Advanced Scientific
Research (JNCASR)

Bangalore, India

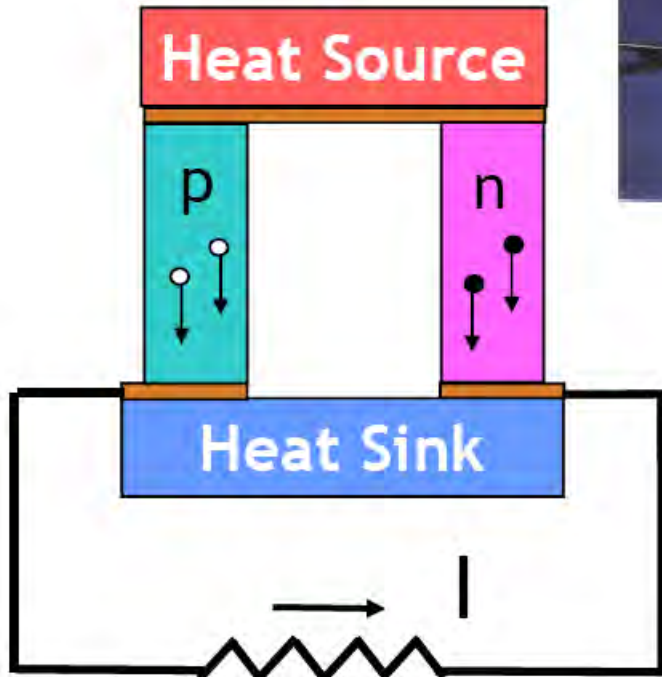
kanishka@jncasr.ac.in



Thermoelectrics (TE)

The thermoelectric effect is the direct conversion of temperature differences to electric voltage and vice versa.

Seebeck Effect

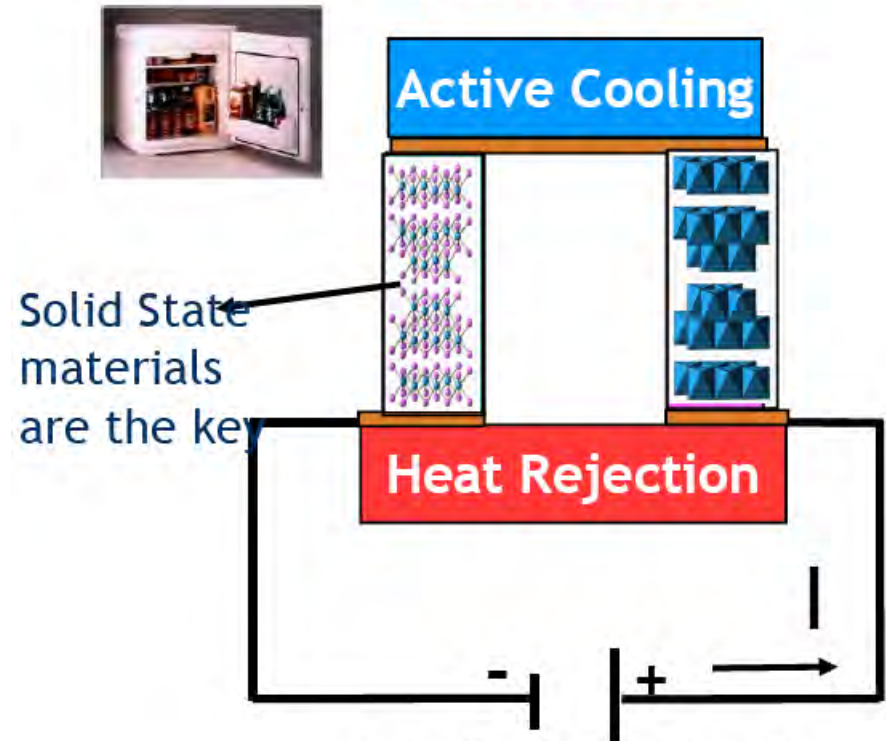


Power Generation Mode

"Electricity from waste-heat"



Peltier Effect



Refrigeration Mode

"Refrigeration without moving parts and chemical refrigerant"

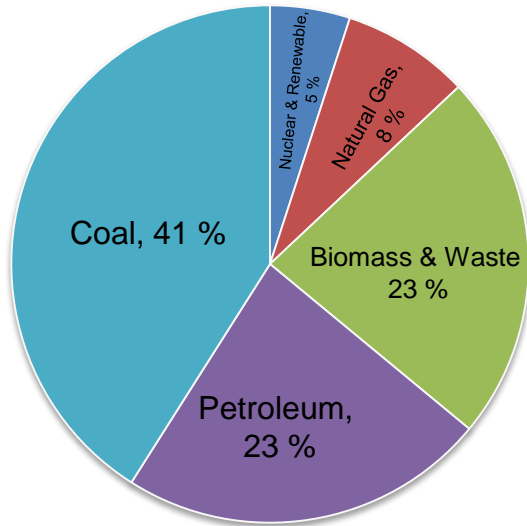


Solid State
materials
are the key

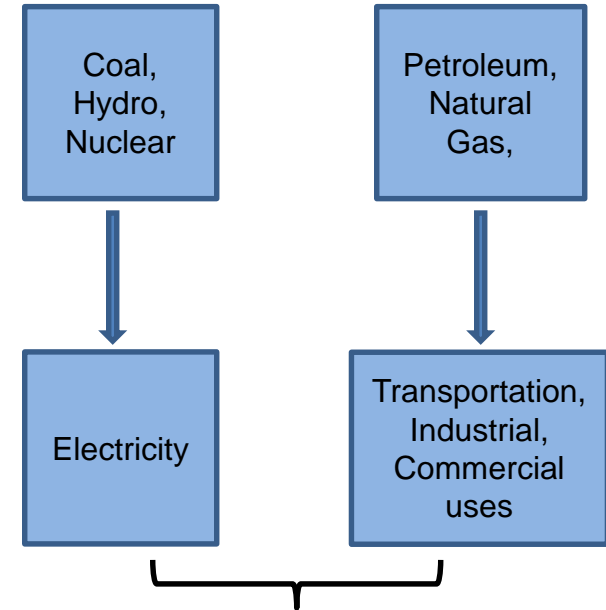
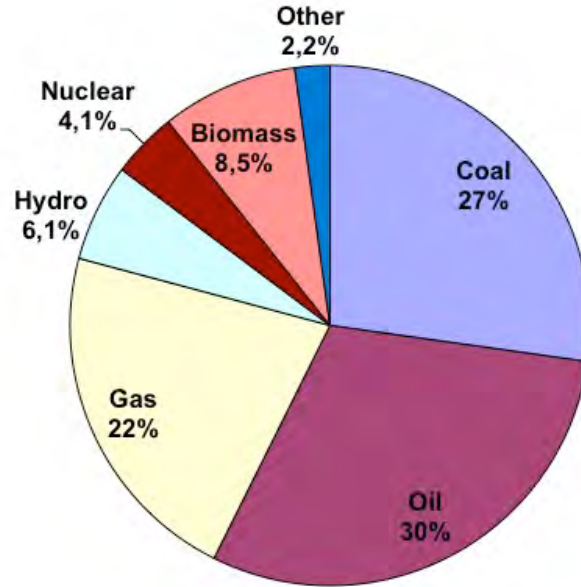
Importance of Thermoelectrics

Total energy consumption

India (2015)



World (2015)



65 % of utilized energy rejected as waste heat

With about ~65 % of the utilized energy being lost as waste heat.

~20 % conversion to the useful form can have significant impact on overall energy utilization.

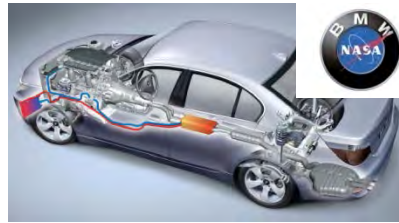
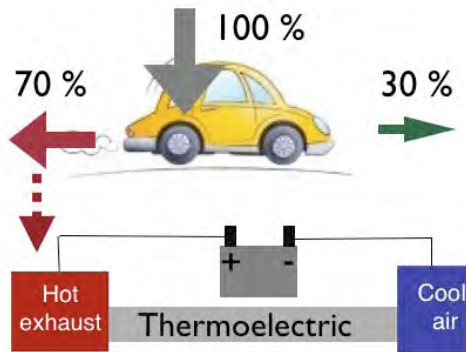
Thermoelectric materials allow the direct conversion between thermal and electrical energy.

Applications

Direct Heat to Electricity Conversion

Waste Heat Recovery/Power generation

- Large scale: Power plant (Chemical/thermal/Nuclear)
- Medium scale: Automobile



Space power generation

Solar-thermoelectrics

Cooling/Refrigeration

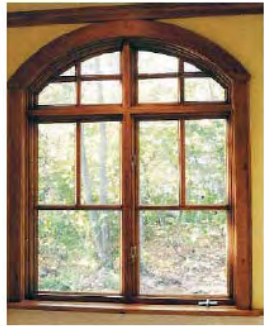
- Commercial cooler/warmer
- Spot cooling: microprocessor, laser diode
- Luxury vehicle: Cool/warm seat



The Mars Science Laboratory rover, Curiosity, is powered by its Radioisotope Thermoelectric Generator.

JPL-Caltech/NASA

Thermoelectric material



Glass

Low thermal conductivity

+



Metal

High electrical conductivity

+



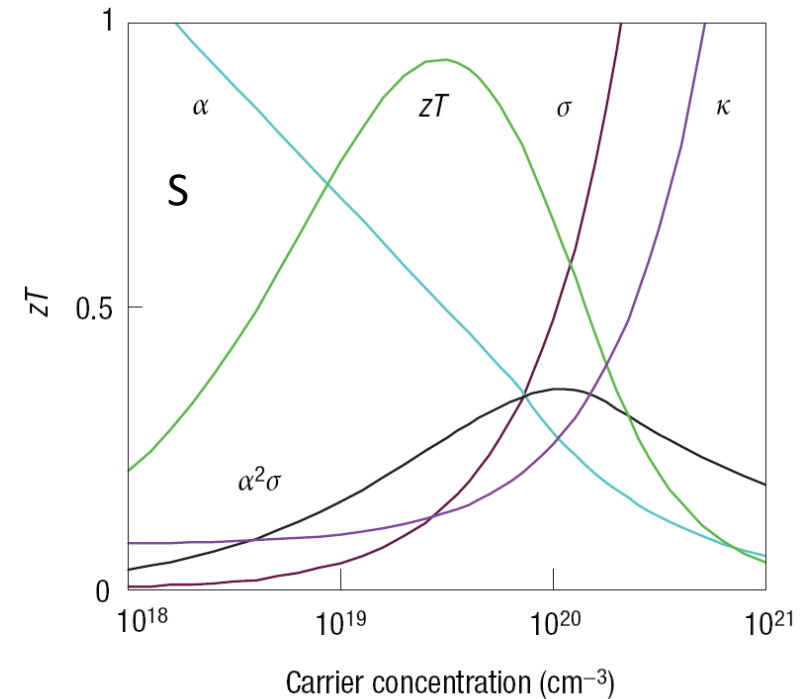
Semiconductor

High Seebeck

Seebeck Coefficient Electrical conductivity

$$ZT = \frac{S^2 \sigma}{K} \cdot T$$

Thermal conductivity (electrical + lattice)

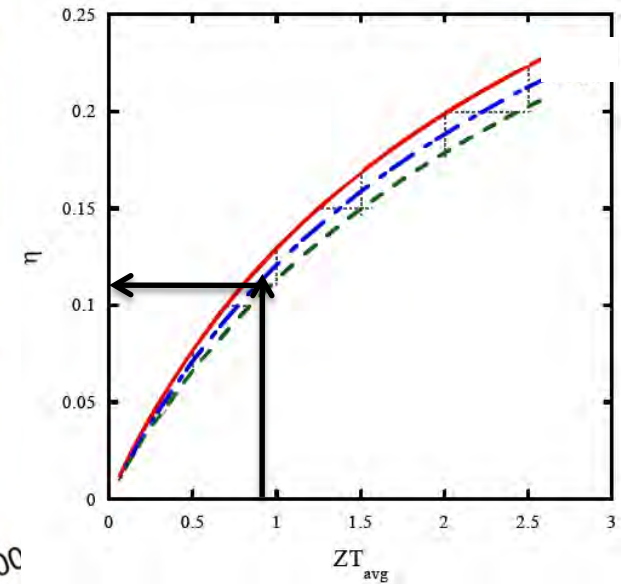
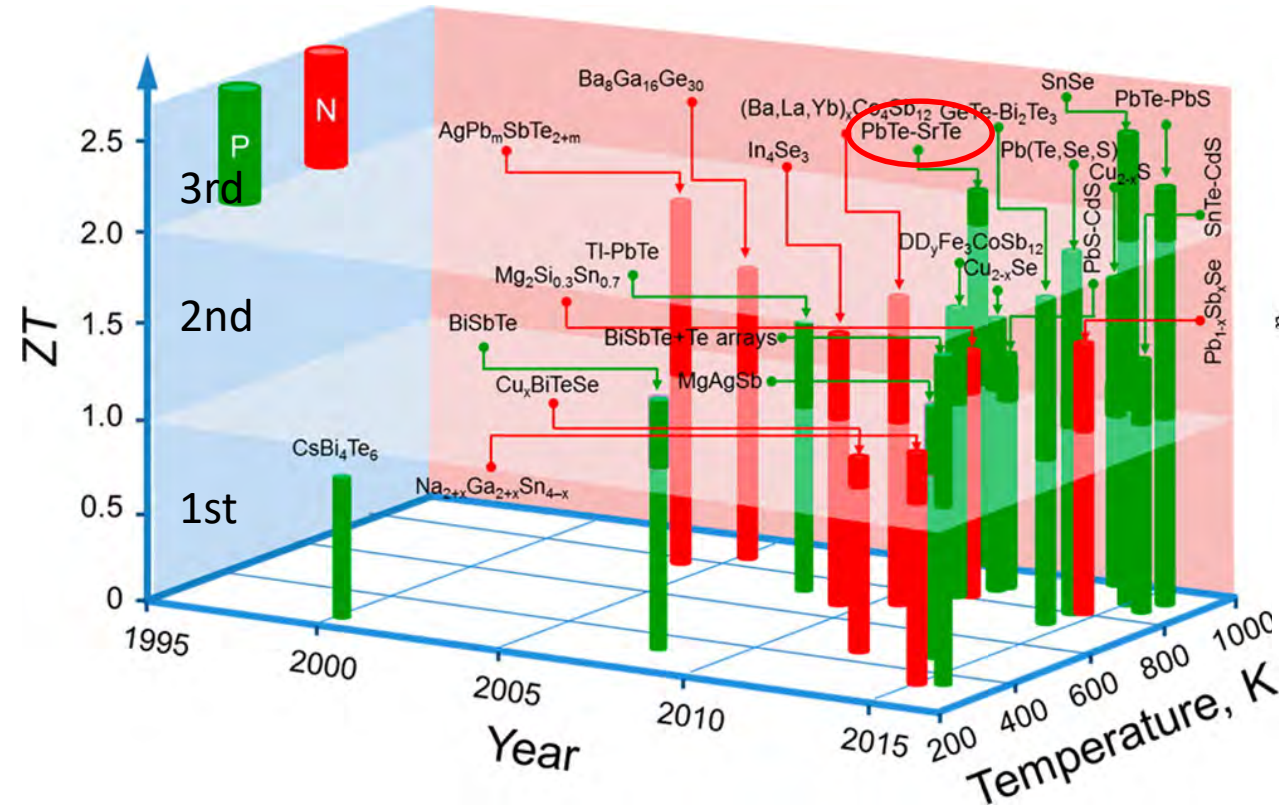


G. J. Snyder and E. S. Toberer, *Nat. Mater.* 2008, **7**, 105-114.

Best thermoelectric materials: Highly doped narrow band gap semiconductor eg. Bi_2Te_3 , PbTe .

Decoupling of electrical and phonon transport is essential for thermoelectrics

State of art thermoelectric bulk materials



Commercial materials in market
 $\eta = 10\%$ with ZT of ≈ 1

G. Tan, L. D. Zhao and M. G. Kanatzidis, *Chem. Rev.* 2016, **116**, 12123.

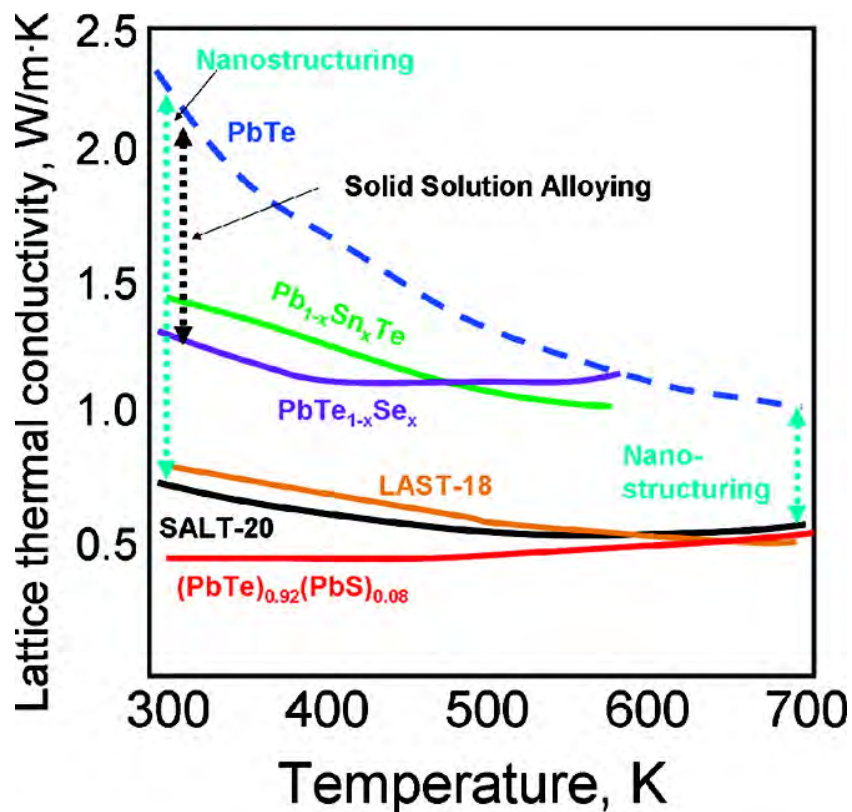
$$\eta = \frac{\Delta T}{T_{hot}} \frac{\sqrt{1 + ZT_{avg}} - 1}{\sqrt{1 + ZT_{avg}} + \frac{T_{cold}}{T_{hot}}}$$

Pb-free high performance materials are desired for mass-market applications

$$ZT = \frac{S^2 \sigma}{\kappa} T$$

Bulk nanostructured thermoelectric materials

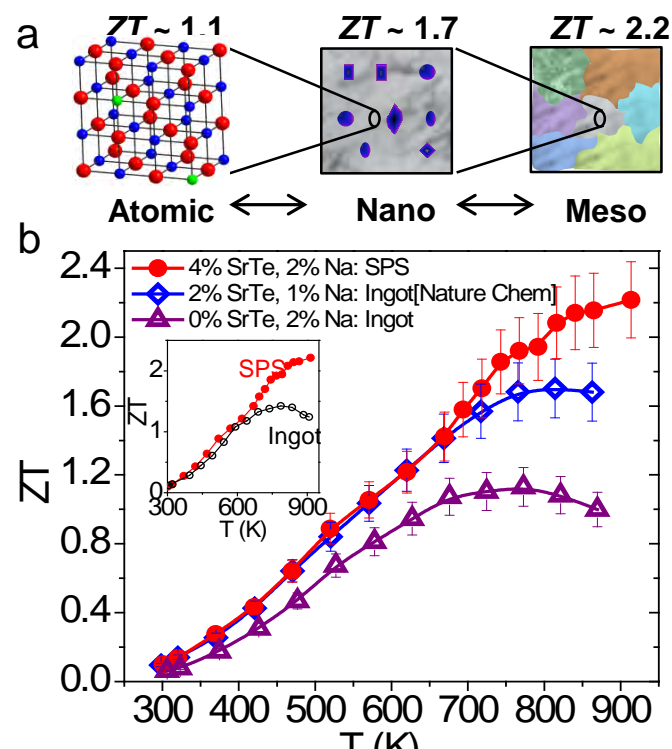
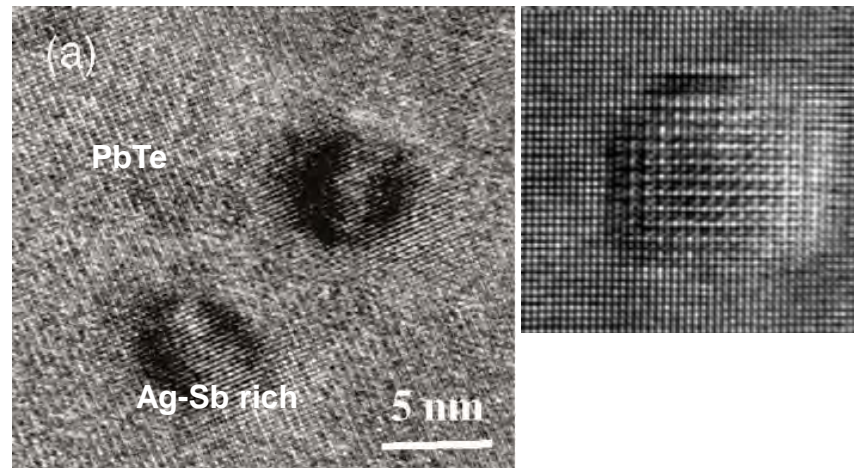
Decrease the thermal conductivity



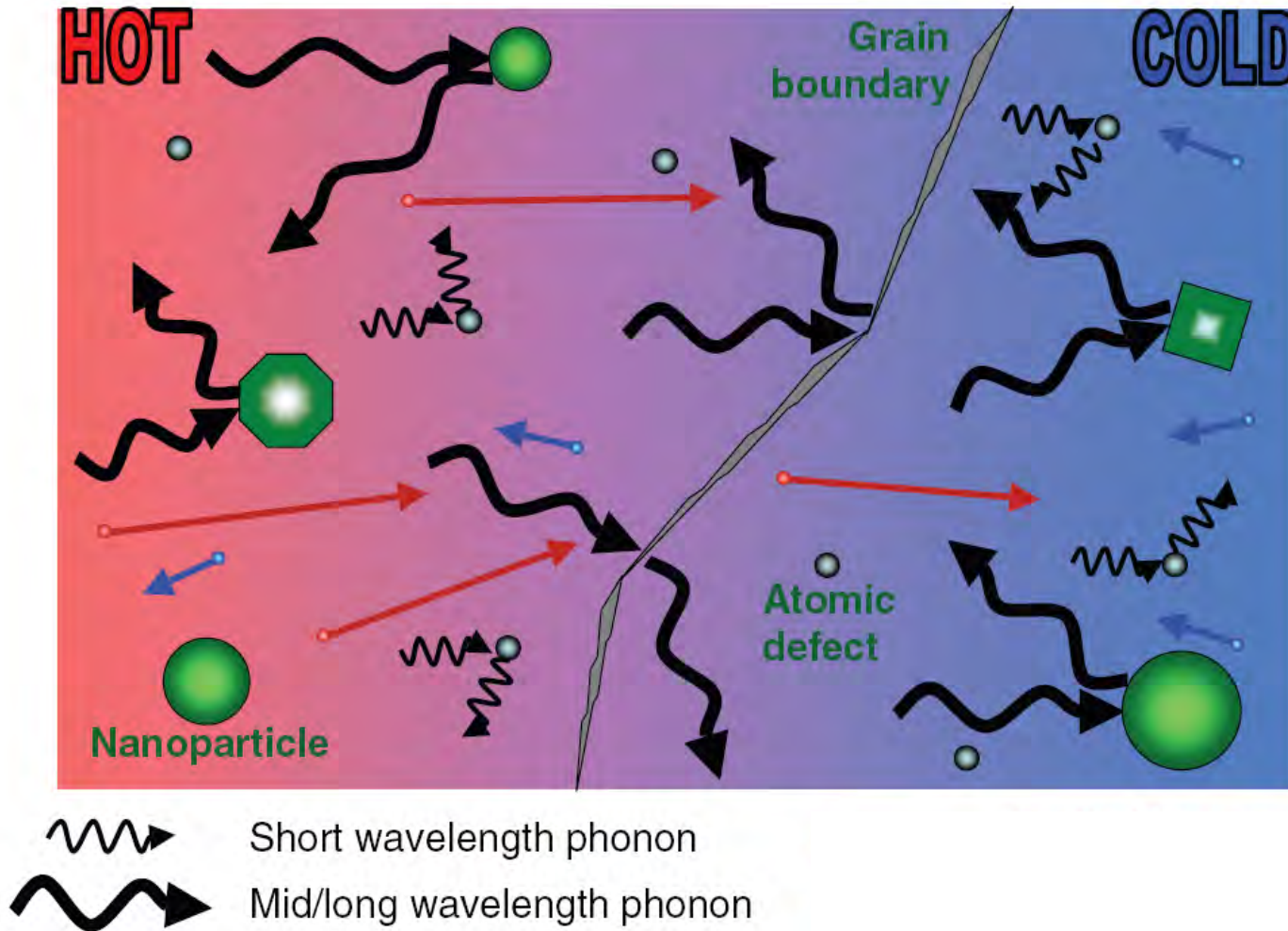
Science 2004, 303, 818-821

Nature 2012, 489, 414-418.

LAST-m ($Ag_{0.86}Pb_{18}SbTe_{20}$) n-type



Phonon scattering mechanism in thermoelectric material



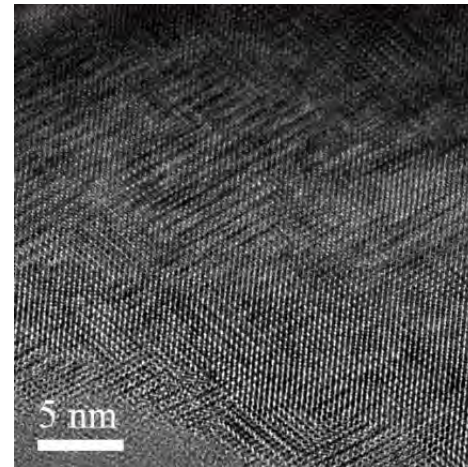
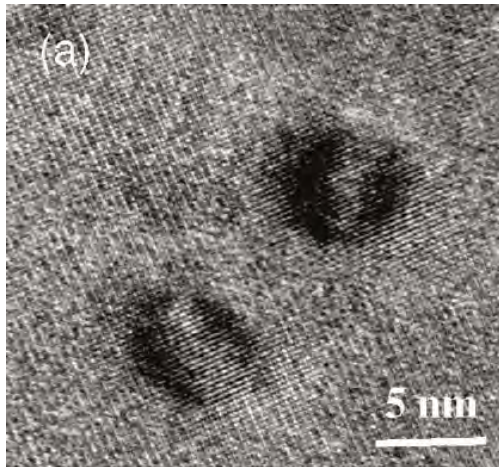
$$\text{Scattering cross section} = d^6/\lambda^4$$

Mid/long wavelength heat-carrying phonon heavily scattered by nanoparticles

Vines, C. J., Shakouri, A., Majumdar, A., Kanatzidis, M. G., *Adv. Mater* **2010**, 22, 3970

$$\Delta G_{\text{mix}} = \Delta H_{\text{mix}} - T\Delta S_{\text{mix}}$$

ΔH of compound formation dominates over ΔS of mixing when nanostructures forms in matrix



Pseudo-ternary vs. pseudo-binary

Nanostructures are good for phonon scattering, but they scatter carrier as well

$$\Delta G_{\text{mix}} = \Delta H_{\text{mix}} - T\Delta S_{\text{mix}}$$

$$\Delta G_{\text{mix}} < 0, \text{ for solid solution}$$

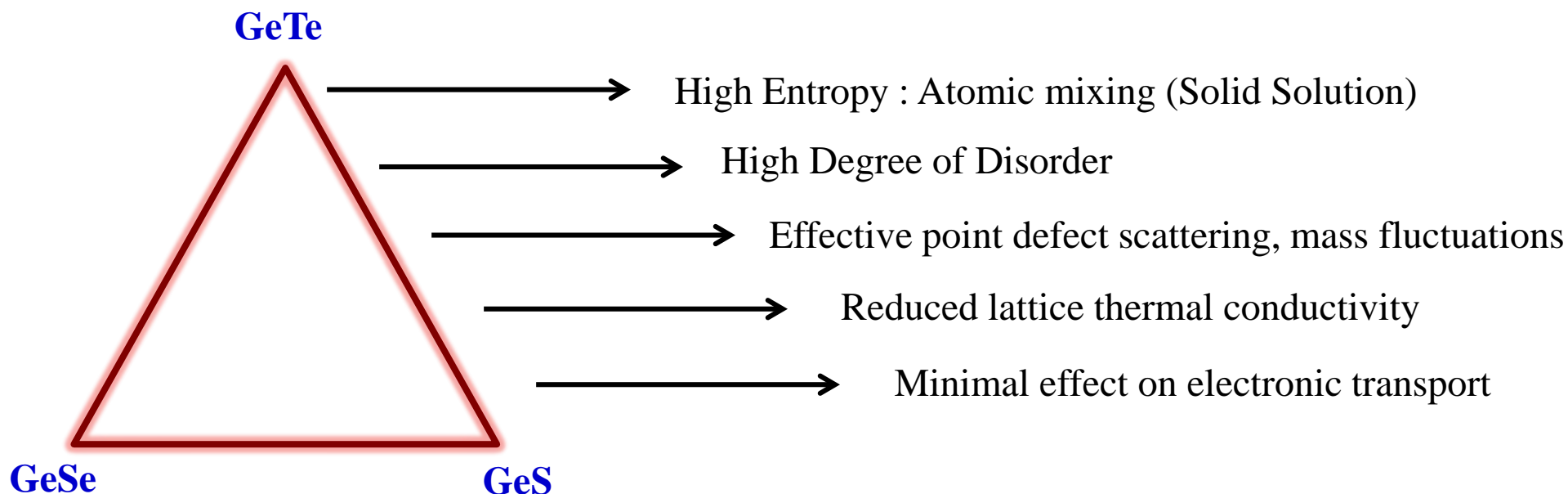
$$\Delta H_{\text{mix}} = H_{\text{solid solution}} - \sum H_{\text{reactant}}$$

$$\Delta S_{\text{mix}} = S_{\text{solid solution}} - \sum S_{\text{reactant}}$$

Enthalpy plays important role over entropy in binary systems (like PbTe/PbSe, GeTe/GeSe and PbTe/PbS), phase separation/nanostructuring can easily occur.

Pseudo-ternary system- Entropy of mixing dominates over enthalpy in ternary system, thus solid solution is favored. Pseudo-ternary system is rich in point defect.

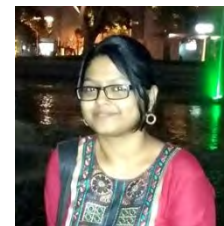
GeTe-GeSe-GeS



Strategy 1: Reduction of κ_{lat} by alloying of GeTe with GeSe and GeS .

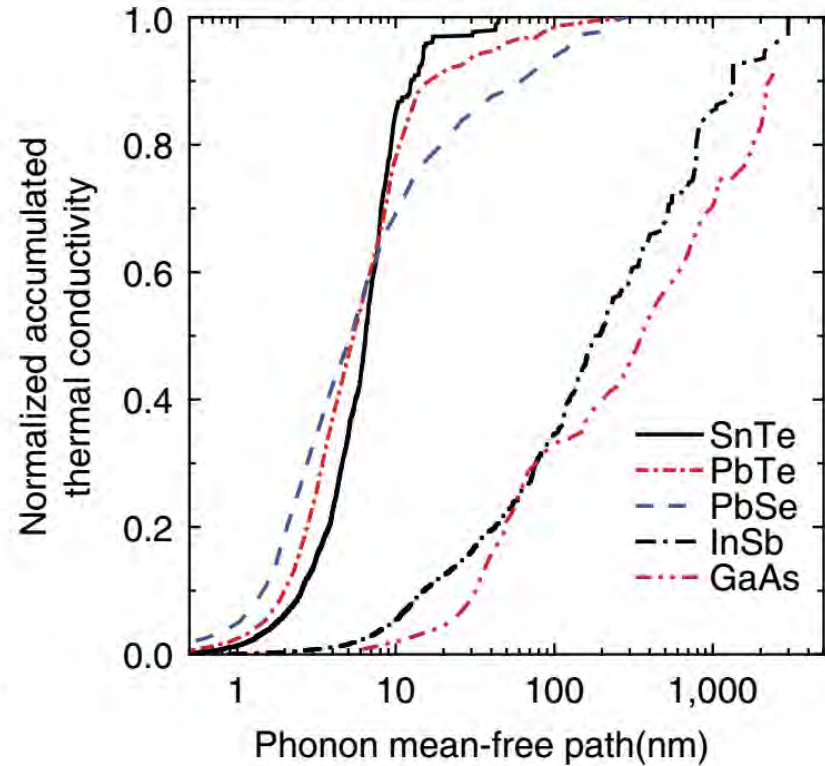
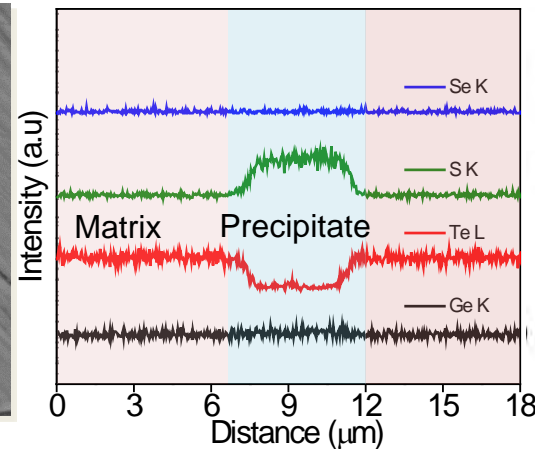
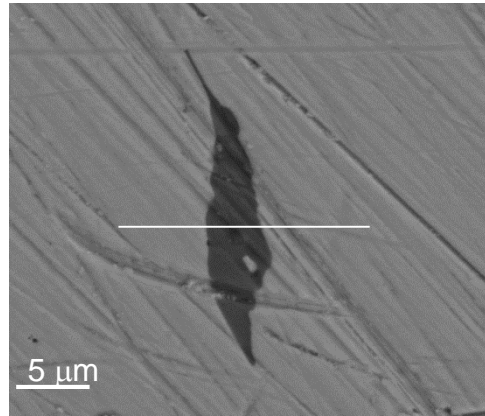
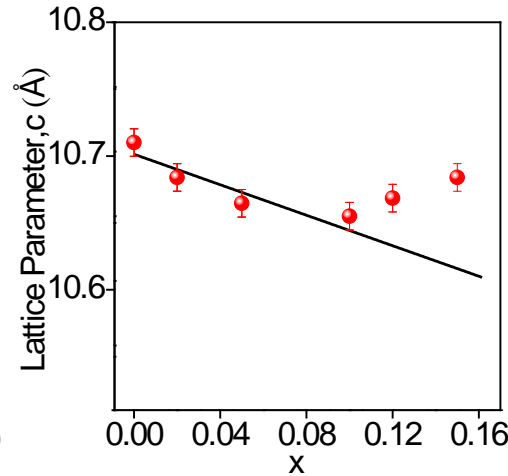
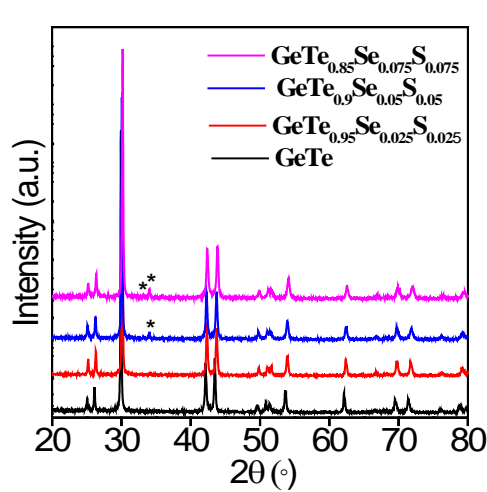
Strategy 2: Further decrease in κ_{lat} by Sb doping in $(\text{GeTe})_{1-2x}(\text{GeSe})_x(\text{GeS})_x$ and by Spark Plasma Sintering.

M. Samanta and K. Biswas, *J. Am. Chem. Soc.* 2017, 139, 9382



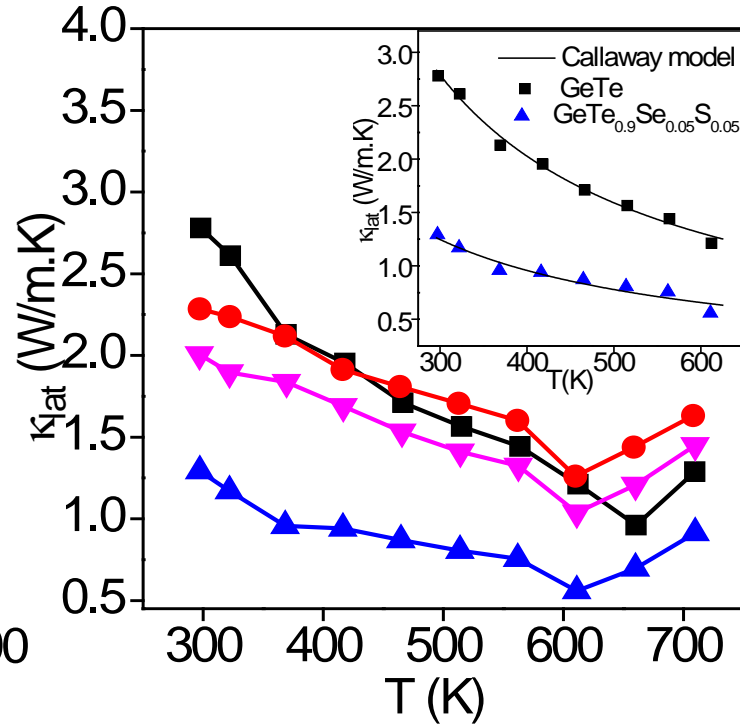
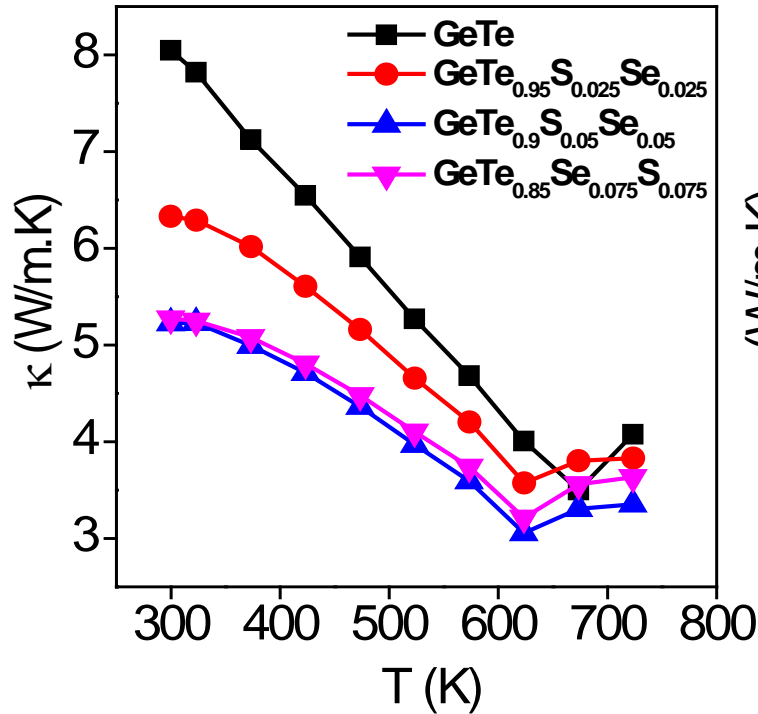
Manisha Samanta

Extended Solid Solution: $(\text{GeTe})_{1-2x}(\text{GeSe})_x(\text{GeS})_x$



Phonons with mean free paths smaller than 10 nm comprise $\sim 90\%$ of the κ_{lat} for IV-VI metal tellurides. (Lee, S.; Esfarjani, K.; Luo, T.; Zhou, J.; Tian, Z.; Chen, G. *Nat. Commun.* **2014**, *5*, 3525.)

Thermal conductivity: Point defect scattering



Callaway Model:

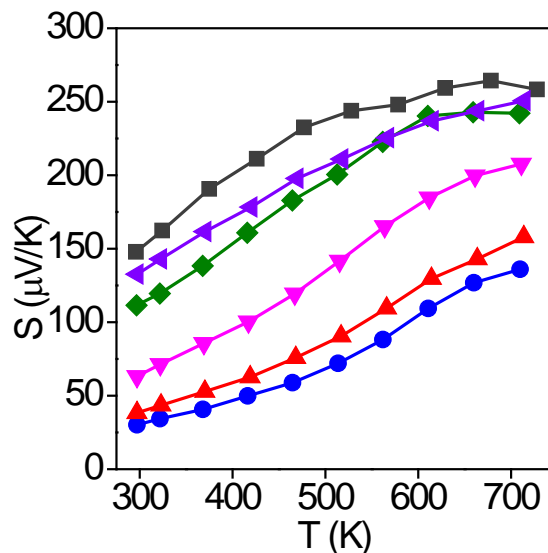
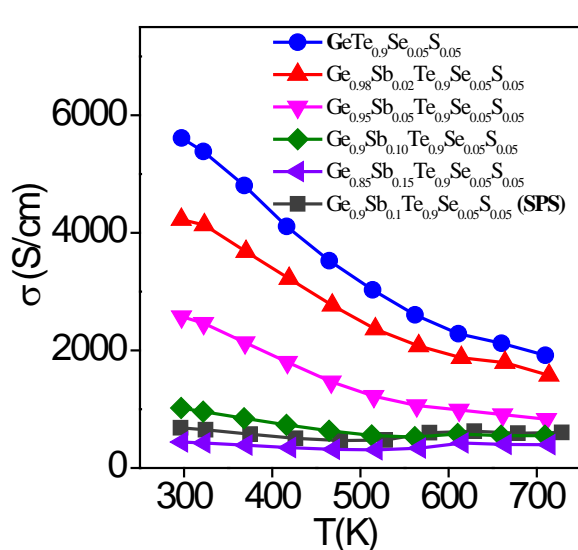
$$k_{lat} = \frac{k_B}{2v\pi^2} \left(\frac{2\pi k_B T}{h} \right)^3 \int_0^{\frac{\theta_D}{T}} \frac{\tau_C(x, T) x^4 e^x}{(e^x - 1)^2} dx$$

$$\tau_C^{-1} = \tau_B^{-1} + \tau_{PD}^{-1} + \tau_U^{-1} + \tau_{ep}^{-1} = \frac{v}{L} + A\omega^4 + B\omega^2 T \exp\left(-\frac{\theta_D}{3T}\right) + C\omega^2$$

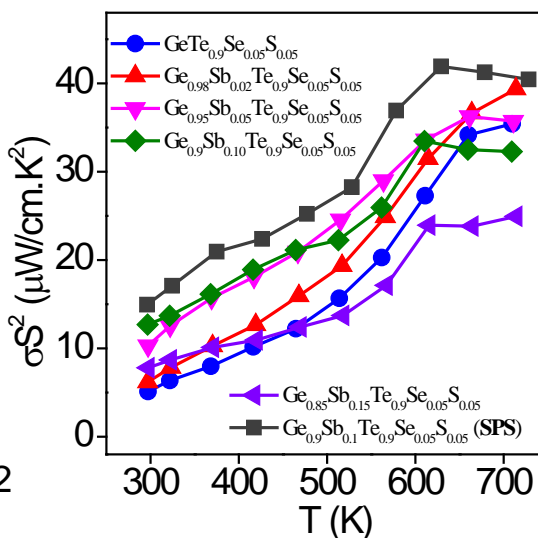
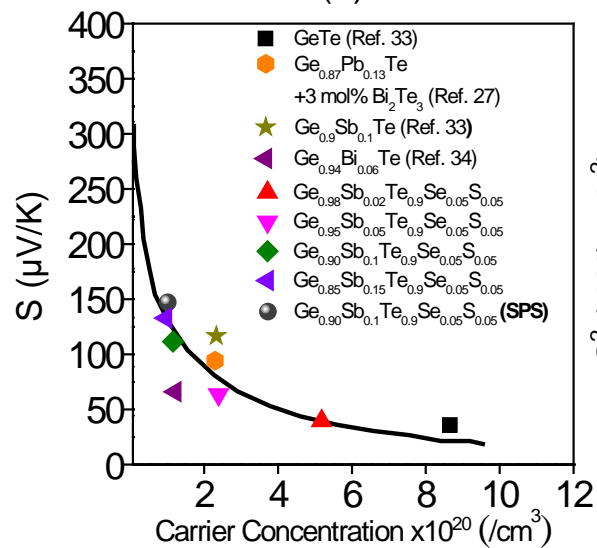
Sample	A [10 ⁻⁴² s ³]	B [10 ⁻¹⁷ s K ⁻¹]
GeTe	1.002	1.18
GeTe _{0.9} Se _{0.05} S _{0.05}	13.9	2.03

Point defect phonon scattering dominates in GeTe_{0.9}Se_{0.05}S_{0.05}

Electrical Transport Properties of Sb doped $\text{GeTe}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$



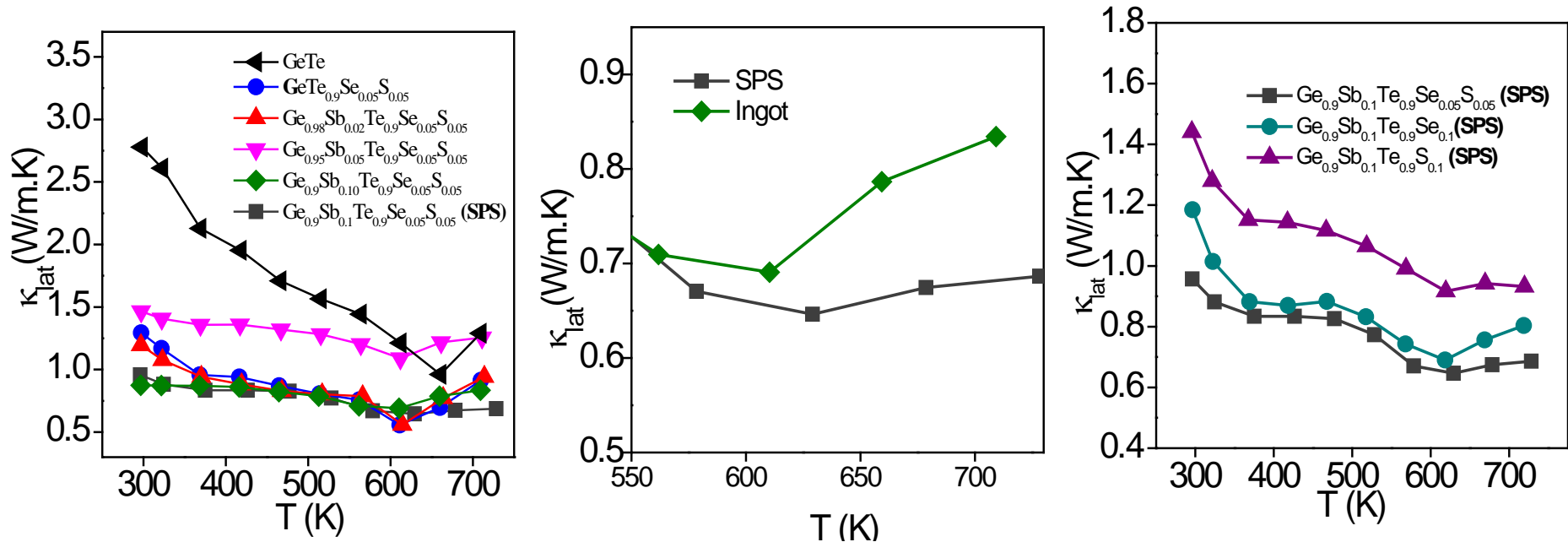
Sample	Carrier concentration (p) $\times 10^{20}/\text{cm}^3$
$\text{Ge}_{0.98}\text{Sb}_{0.02}\text{Te}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$	5.18
$\text{Ge}_{0.95}\text{Sb}_{0.05}\text{Te}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$	2.39
$\text{Ge}_{0.90}\text{Sb}_{0.1}\text{Te}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$	1.16
$\text{Ge}_{0.90}\text{Sb}_{0.1}\text{Te}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$ (SPS)	1.02
$\text{Ge}_{0.85}\text{Sb}_{0.15}\text{Te}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$	0.96



- Seebeck Coefficient increases with Sb doping
- Electrical conductivity decreases with Sb doping

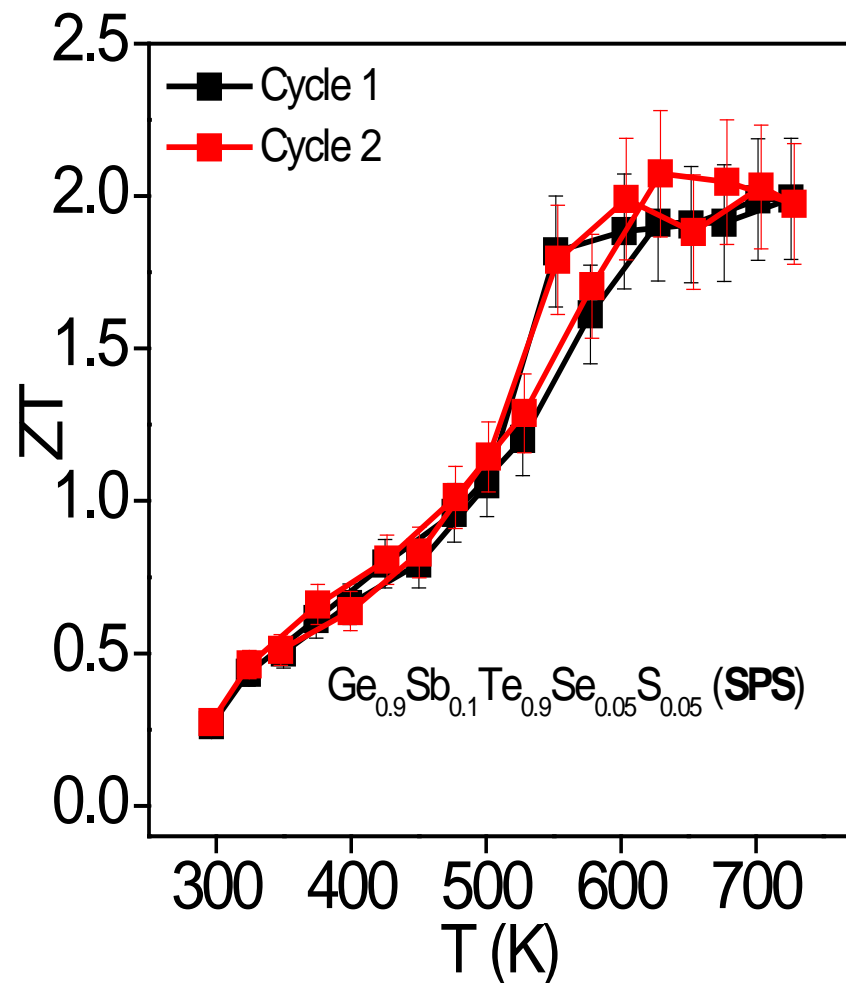
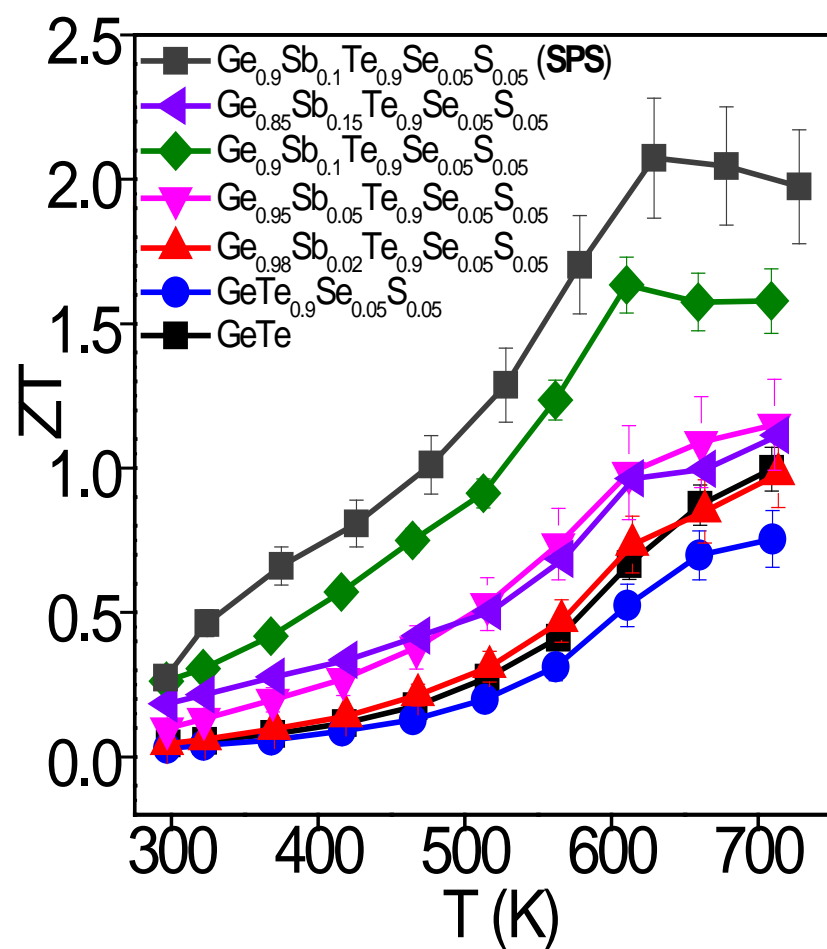
Low lattice thermal Conductivity in $(\text{GeTe})_{1-2x}(\text{GeSe})_x(\text{GeS})_x$

Pseudo-ternary vs. pseudo-binary



- Low $k_{\text{lat}} \sim 0.7$ W/mK is achieved in $\text{Ge}_{0.9}\text{Sb}_{0.1}\text{Te}_{0.9}\text{Se}_{0.05}\text{S}_{0.05}$ (SPS).
- GeTe-GeSe-GeS pseudo ternary system shows lower k_{lat} than GeTe-GeSe and GeTe-GeS pseudo binary system.
- Phonon scattering mainly occurs due to effective point defect scattering involving a broad set of multiple types of mass fluctuations such as Ge/Sb, Te/Se, Te/S and Se/S.

ZT = 2.1 in Pb free GeTe based system



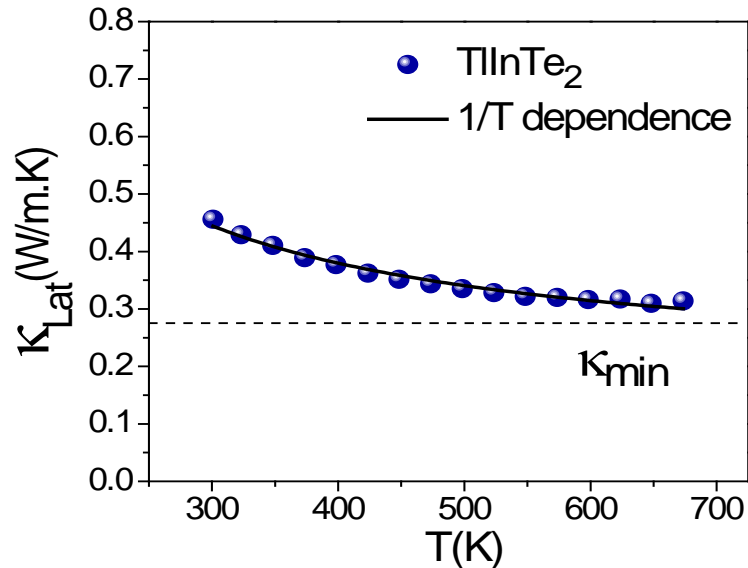
M. Samanta, K. Biswas, *J. Am. Chem. Soc.* 2017, 139, 9382

Extrinsic approach- Introduction of point defects, nanoprecipitates and grain boundaries.

They scatters the phonons heavily, **but scatters the electrons/holes as well.**

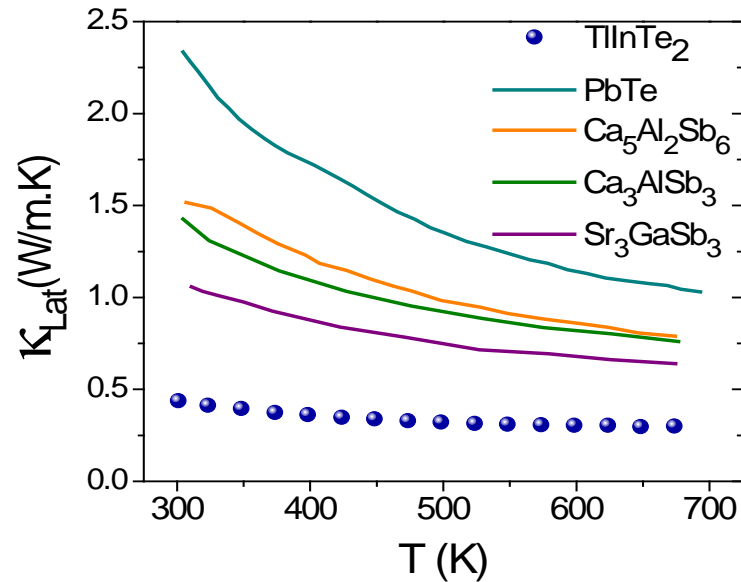
Intrinsic low thermal conductivity is of practical interest due to its robustness against grain size, temperature range and other structural variations.

Ultralow Thermal Conductivity in Zintl Type TlInTe_2



Slack's formalism (at high T)

$$\kappa_{\text{Lat}} = \frac{A \bar{M} \theta^3 \delta}{\gamma^2 n^{2/3} T}$$



Cahill's minimum thermal conductivity

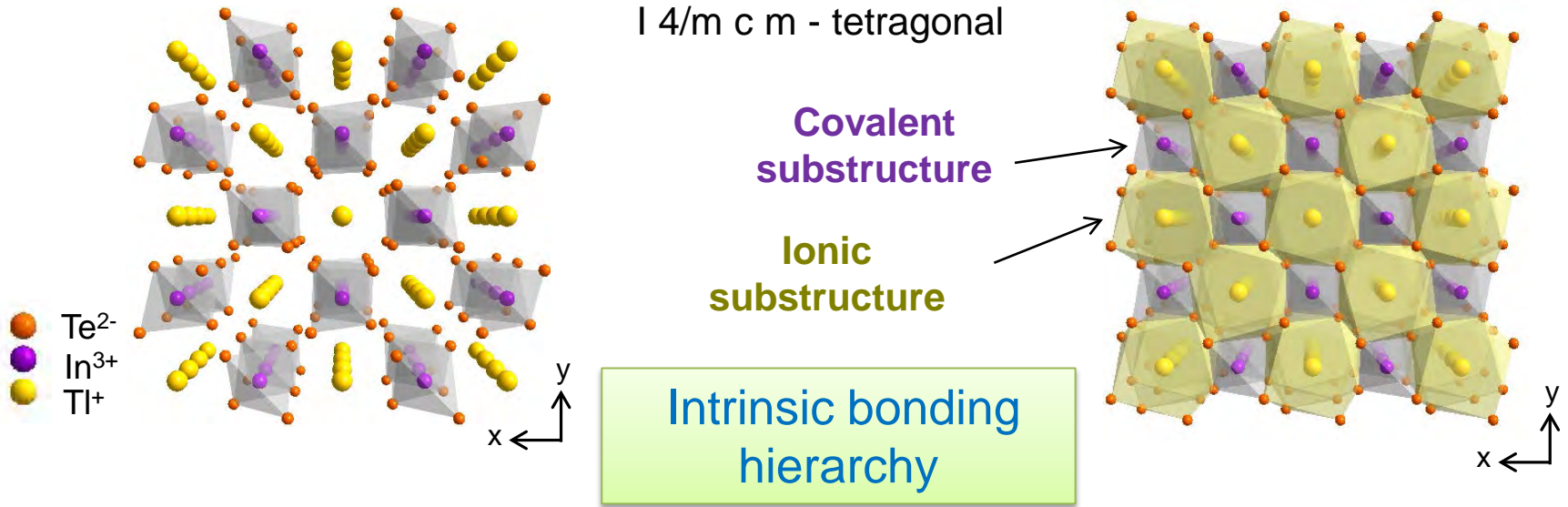
$$\kappa_{\text{min}} = \left(\frac{\pi}{6}\right)^{1/3} k_B n_a^{2/3} \sum_i v_i \left(\frac{T}{\theta_i}\right)^2 \int_0^{\theta_i/T} \frac{x^3 e^x}{(e^x - 1)^2} dx$$

- $1/T$ dependence of lattice thermal conductivity suggests dominant anharmonic Umklapp phonon scattering.
- Ultralow lattice thermal conductivity approaching theoretical amorphous-limit (κ_{min}) at high temperatures.

Intrinsic Rattler-Induced Low Thermal Conductivity in Zintl Type TlInTe_2

Crystal structure of TlInTe_2

$I 4/m c m$ - tetragonal



- Anionic and cationic substructures resembling 1D-zintl compounds
- Covalently bonded chains of (InTe_4) tetrahedra along the z-axis (violet)
- Each TI^+ cation is centered in a distorted square antiprism of Te ions (Thompson cubes)
- Anionic chains are held electrostatically by chains of TI^+ cations.

Ultralow Thermal Conductivity in Zintl Type TlInTe_2

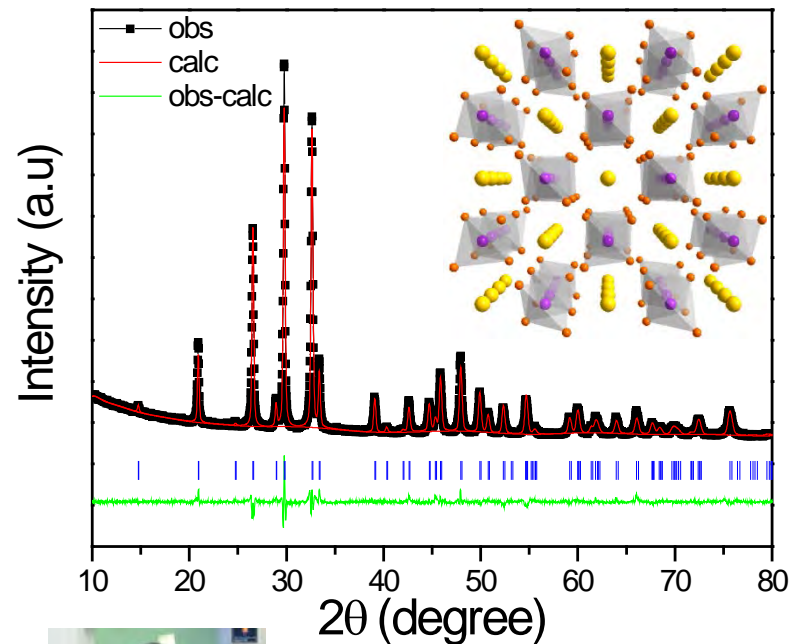
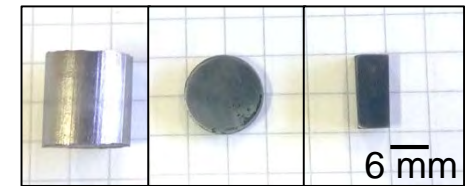
Synthesis

7 hr
(TI, In, Te)
Fused quartz ampoules (10^{-5} torr)

10 hr
1123 K

15 hr
(TlInTe_2)

SPS
50 MPa, 723 K,



Manoj

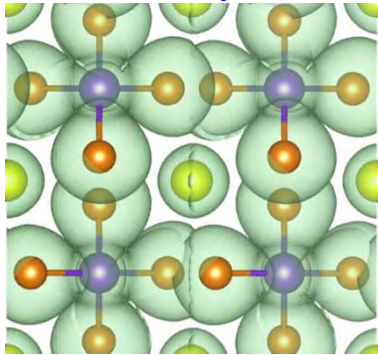
Structural parameters from Rietveld refinement

	a	b	c	Vol (\AA^3)
I4/mcm	8.47980 (27)	8.47980 (27)	7.18894 (28)	516.94 (5)
	x	y	z	U_{iso} (\AA^2)
In	0	0.5	0.25	0.01674
Te	0.18098	0.68098	0	0.0235
				U_{11} U_{22} U_{33}
Tl	0	0	0.25	0.02759 0.02759 0.07442

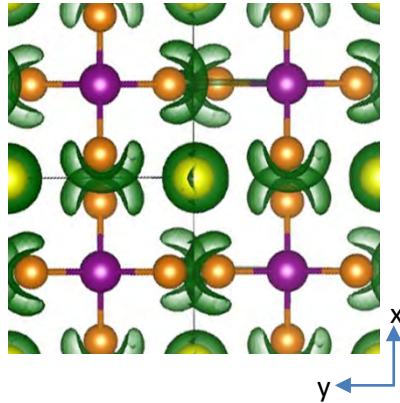
Anisotropic, large atomic displacement parameters (ADPs) of Tl^+

Structure and bonding in TlInTe_2

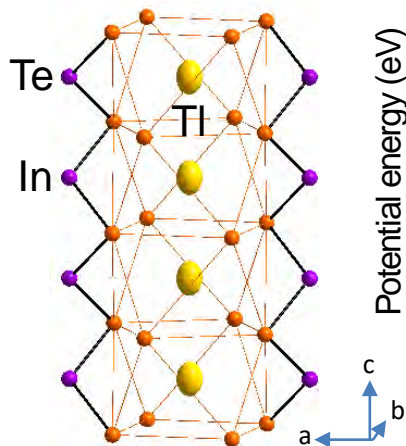
Valence charge density



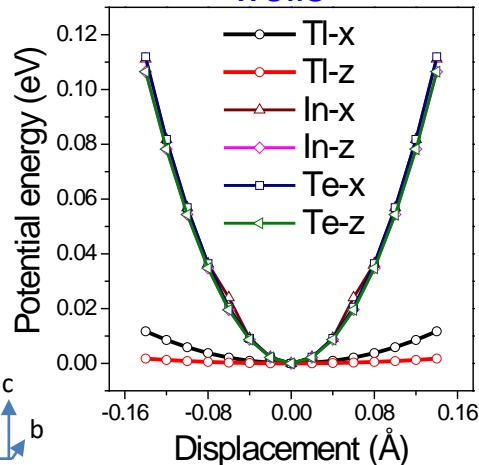
Electron localization



ADP ellipsoids (80% probability)



Potential energy wells



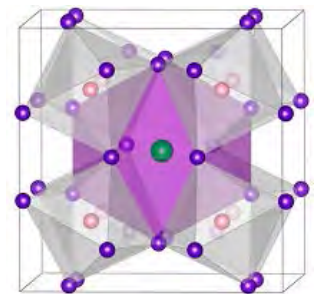
- Covalent bonding within (InTe_4) tetrahedron and isolated Tl^+ cations.
- Spherical charge density around Tl^+ cation $\rightarrow 6s^2$ lone electron pair
- Spherical lone pairs are unstable and are known to form stereochemical lobes by distorting the structure.

(e.g. *Lone-pair driven monoclinic distortion of perovskite BiMnO_3*)

- Steep potential wells for In and Te atoms but flat potential well for Tl atoms
- No apparent distortion in the average structure
- Consequently, phonons may be highly anharmonic

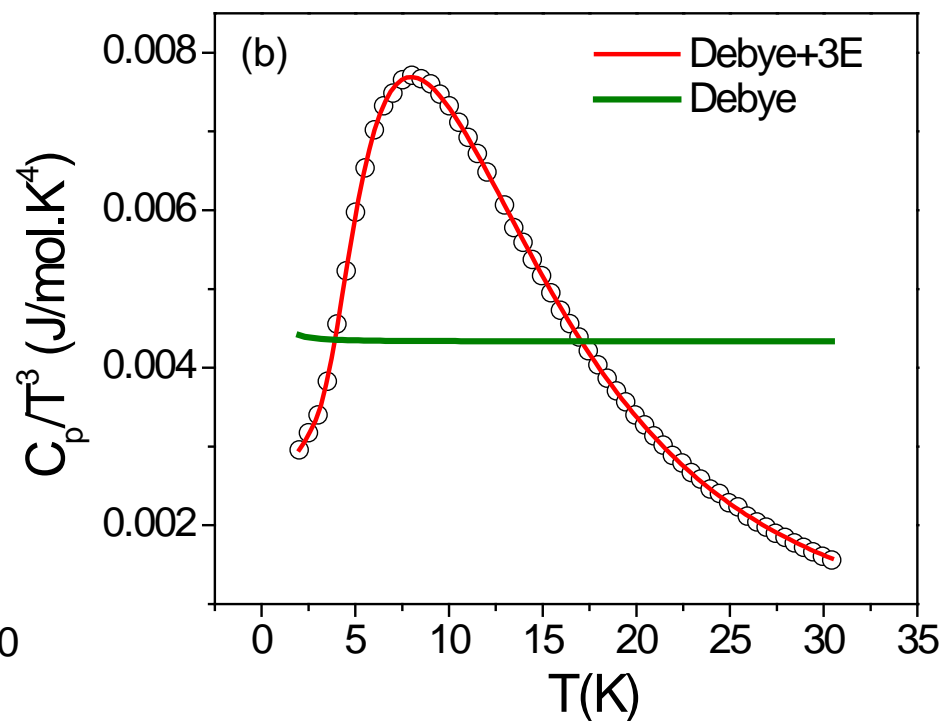
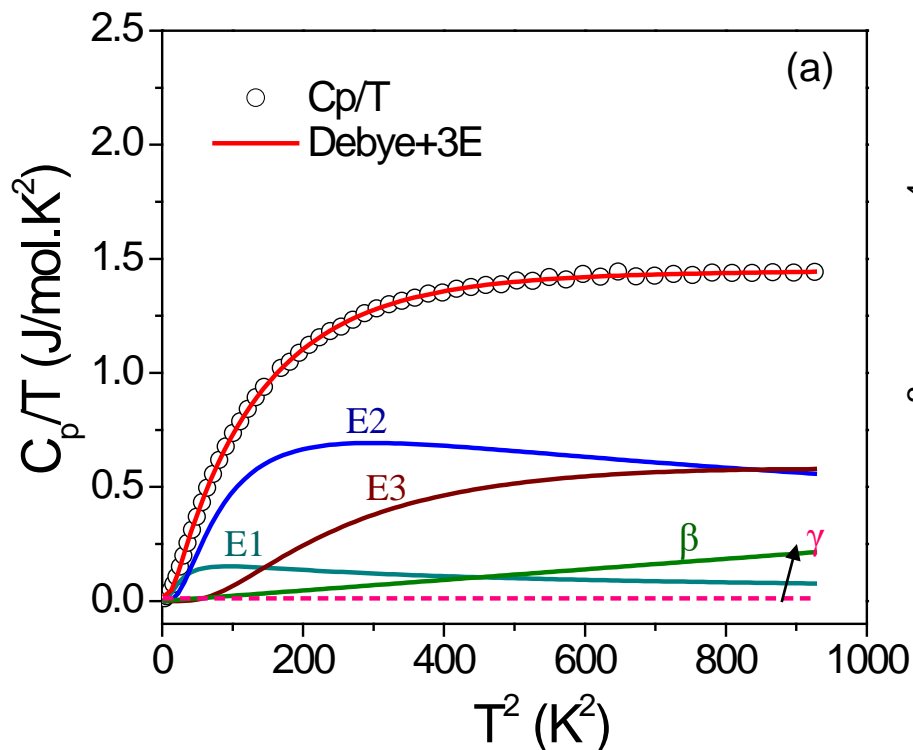
(Nielsen et al, *Energy Environ. Sci.* **2013**, 6, 570)

Tl - intrinsic rattler



Filled-skutterudite

Low temperature heat capacity of TlInTe₂

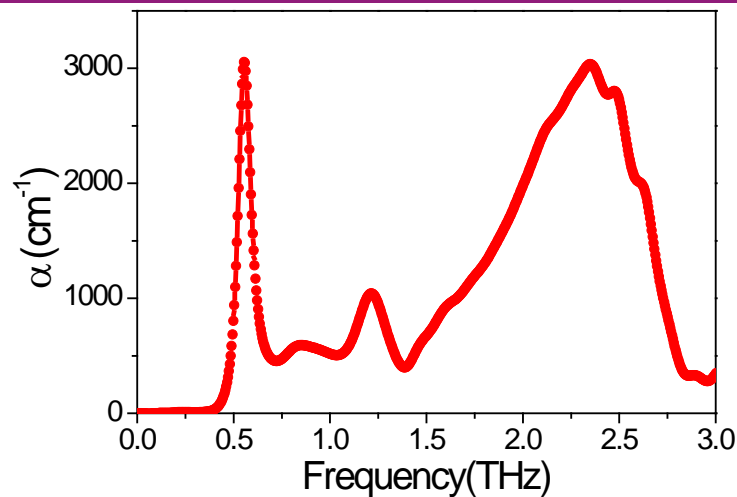


Debye-Einstein model

$$C_P/T = \gamma + \beta T^2 + \sum_i \left(A_i (\Theta_{E_i})^2 \cdot (T^2)^{-\frac{3}{2}} \cdot \frac{e^{\frac{\Theta_{E_i}}{T}}}{(e^{\frac{\Theta_{E_i}}{T}} - 1)^2} \right)$$

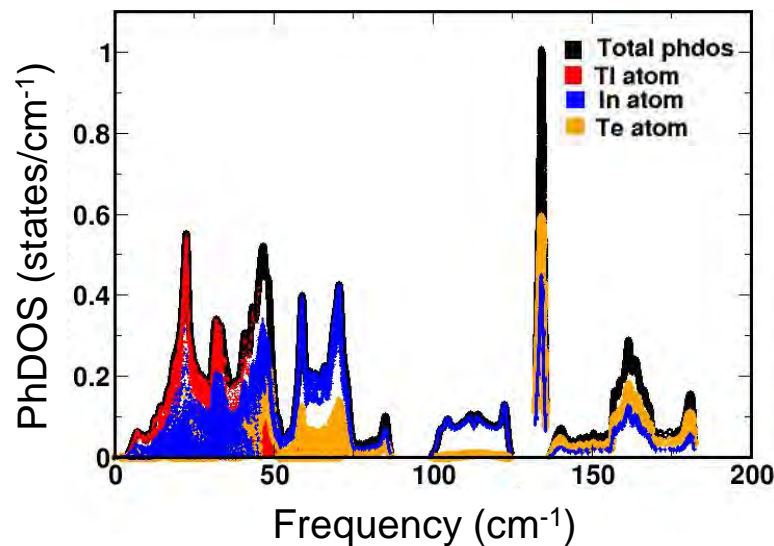
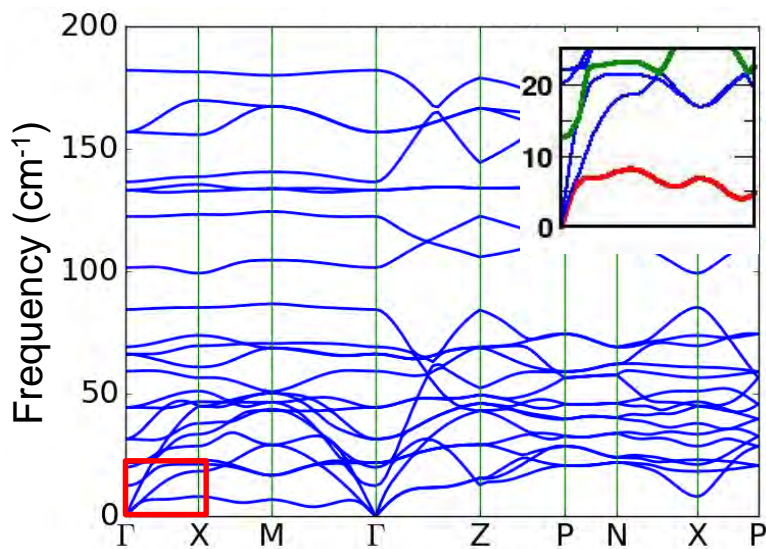
- Low temperature specific heat capacity shows the contribution of Einstein oscillators with frequencies of about 17, 30 and 55 cm⁻¹
- The low-energy Einstein modes are related to low-frequency, localized optic-like vibrations. The latter can scatter the heat-carrying acoustic phonons and suppress thermal conductivity significantly.

THz spectra of TlInTe_2



Pankaj Mandal, IISER, Pune

Phonon dispersion of TlInTe_2

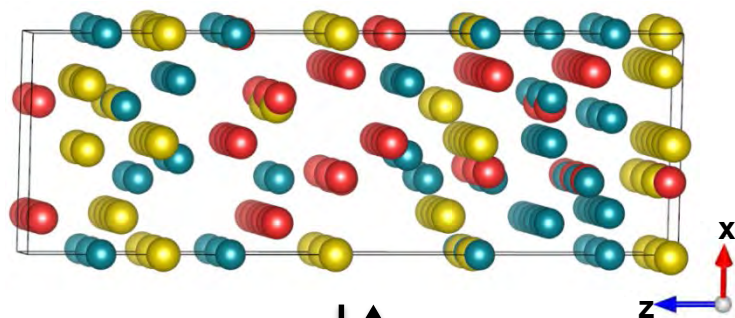


Umesh Waghmare, JNCASR, Bangalore

Soft Phonon Modes Leading to Ultralow Thermal Conductivity and High Thermoelectric Performance in AgCuTe

Crystal Structure of AgCuTe

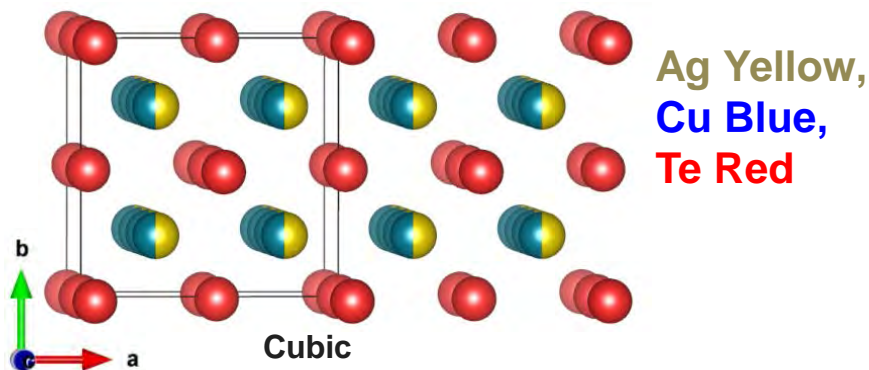
Hexagonal



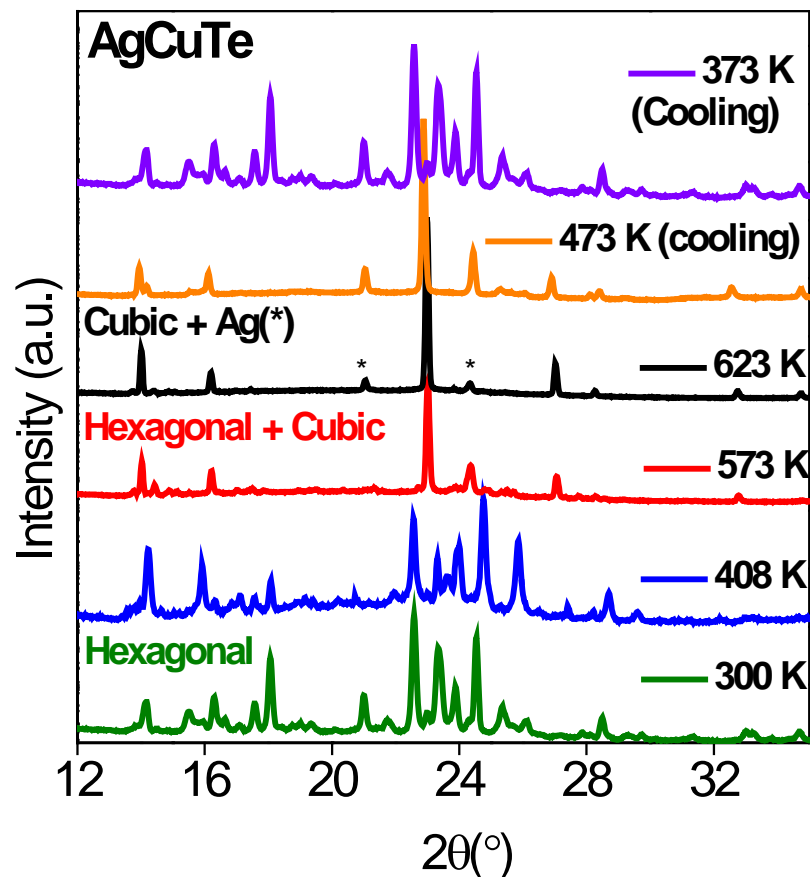
Heating



cooling



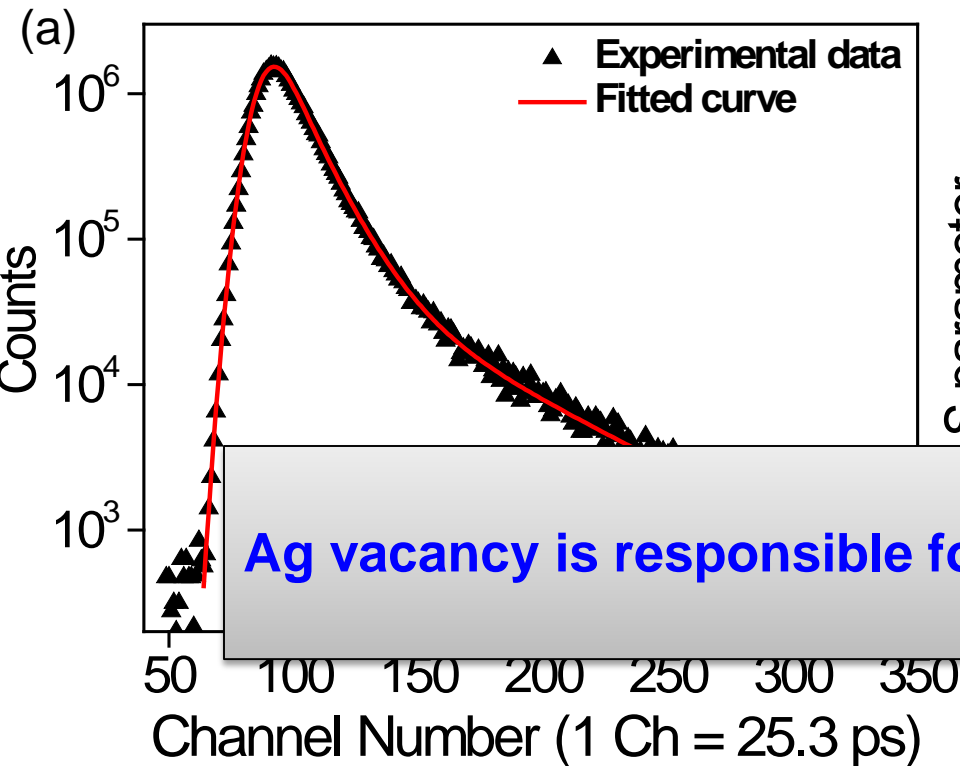
synchrotron experiments at the Indian Beamline, **PF, KEK, Japan**



S. Roychowdhury, M. K. Jana, J. Pan, S. N. Guin, D. Sanyal, U. V. Waghmare, K. Biswas,
Angew. Chem. Int. Ed. 2018, 57, 4043

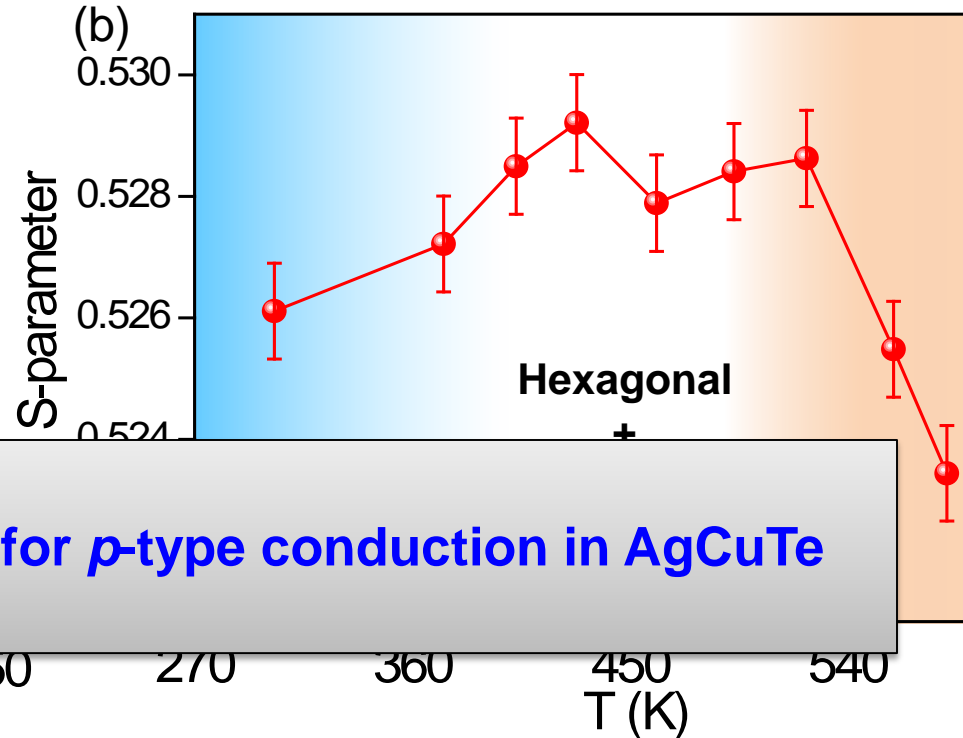
Positron annihilation spectroscopy: Role of Ag vacancy

Positron annihilation Lifetime Spectrum



Lifetime component: 304 ± 3 ps :
Ag Vacancy

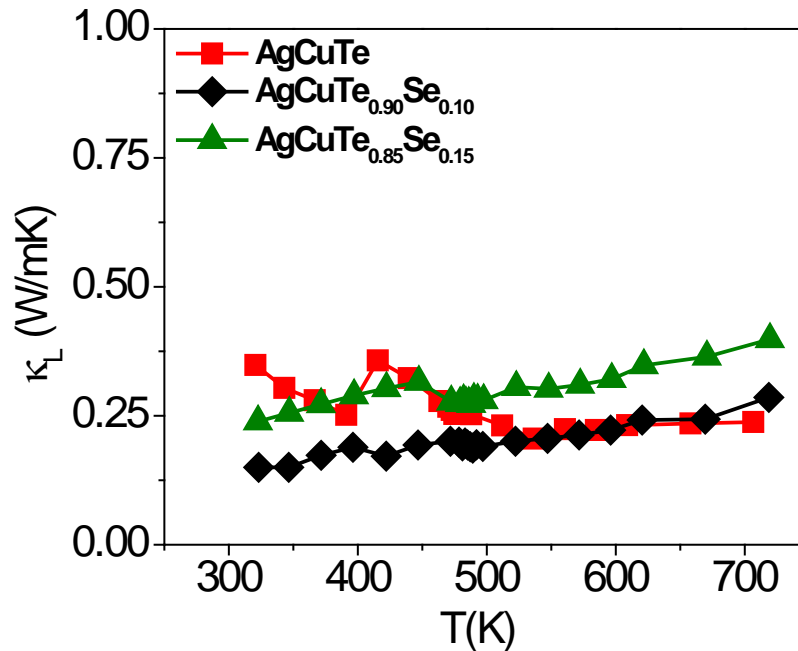
Doppler broadened spectrum



Vacancies act like “hole” channels for
superionic conduction of cations

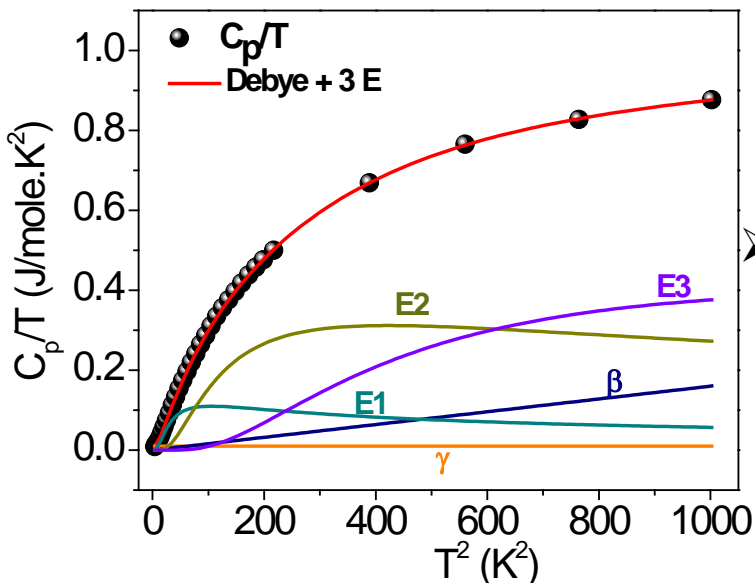
The S-parameter represents the fraction of positrons annihilating with the low-momentum valence electrons with respect to the total number of positrons annihilated

Ultralow thermal conductivity



Subhajit
Roychowdhury

Low-T Heat Capacity for AgCuTe

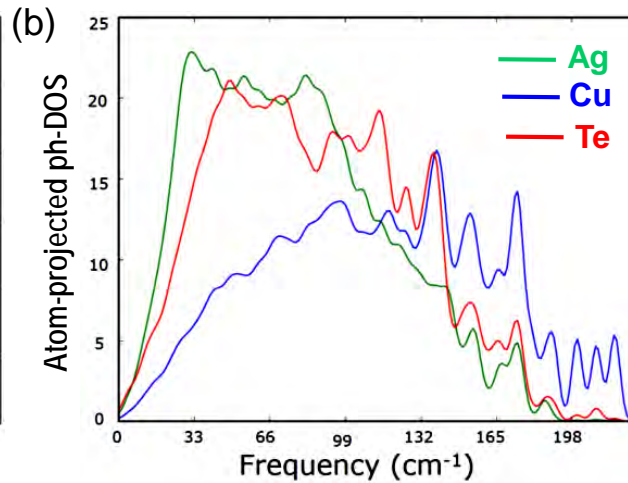
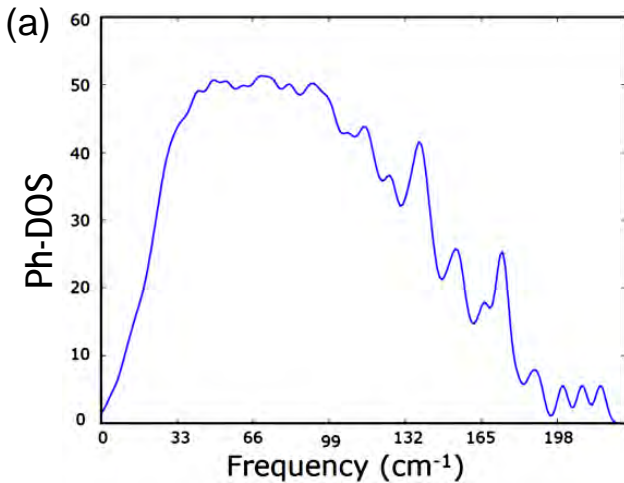


Debye-Einstein model

$$C_P/T = \gamma + \beta T^2 + \sum_i \left(A_i (\Theta_{E_i})^2 \cdot (T^2)^{-\frac{3}{2}} \cdot \frac{e^{\frac{\Theta_{E_i}}{T}}}{\left(e^{\frac{\Theta_{E_i}}{T}} - 1 \right)^2} \right)$$

- The low-energy Einstein modes (26, 52 and 103 cm⁻¹) are related to low-frequency, localized optic-like vibrations which can scatter the heat-carrying acoustic phonons and suppress thermal conductivity significantly.

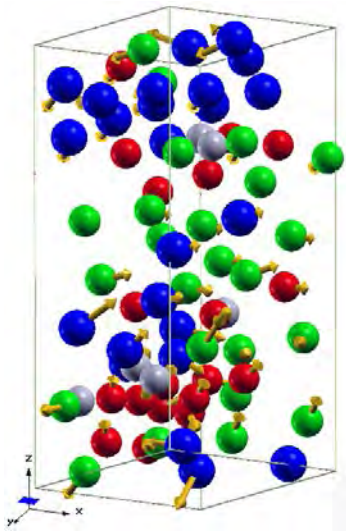
Phonon Density of States



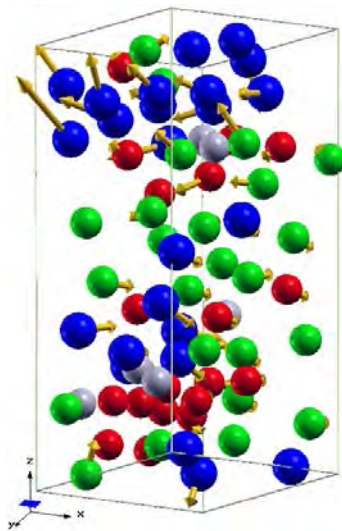
Ph-DOS of the hexagonal phase reveals unusually many “soft” vibrational modes with frequencies lower than 50 cm^{-1}

Dominant contributions from Ag ionic displacements

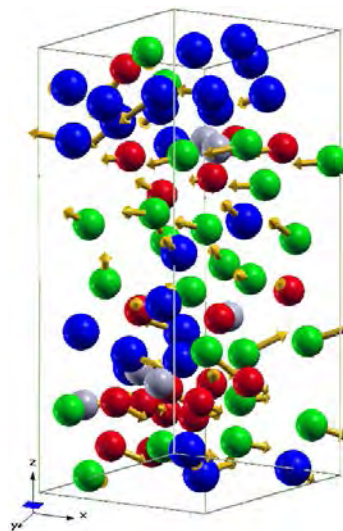
(c)



Mode 1 (5.14 cm^{-1})



Mode 2 (9.45 cm^{-1})

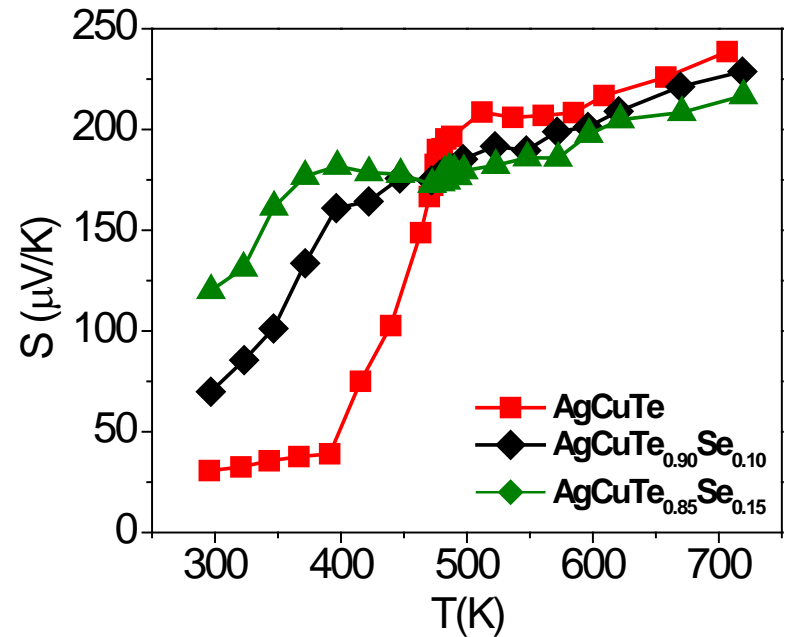
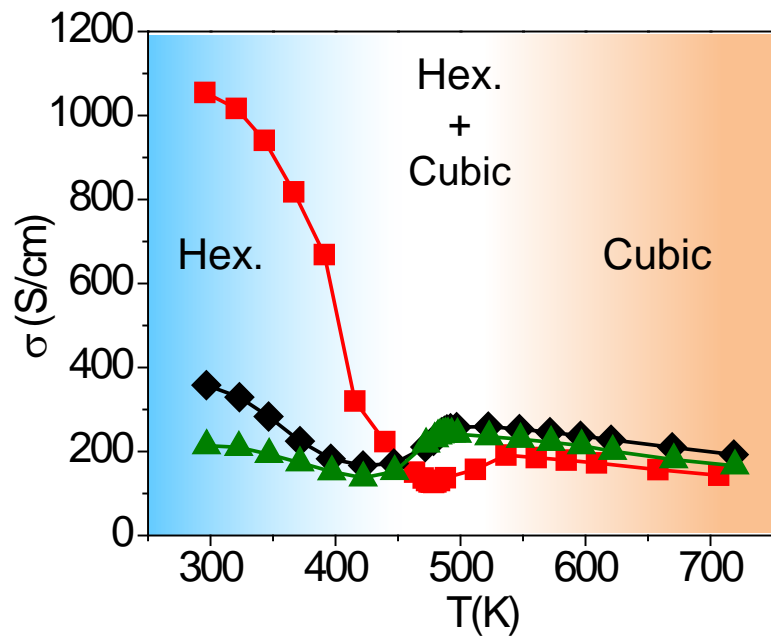


Mode 3 (12.65 cm^{-1})

Optical-acoustic phonon coupling

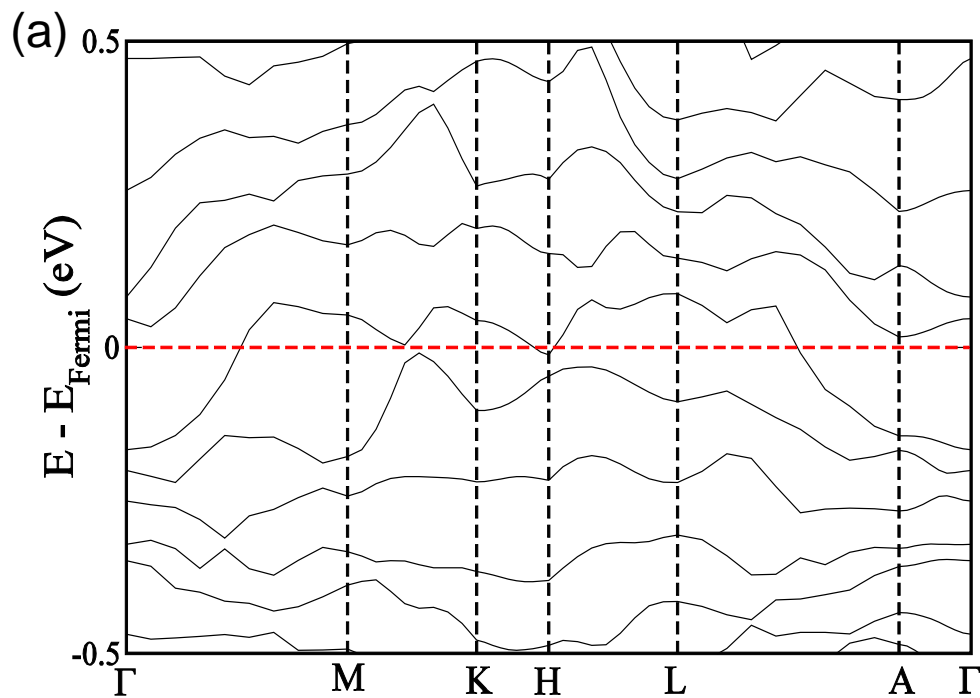
Ag blue, Cu red, Te green

Electronic transport properties of AgCuTe

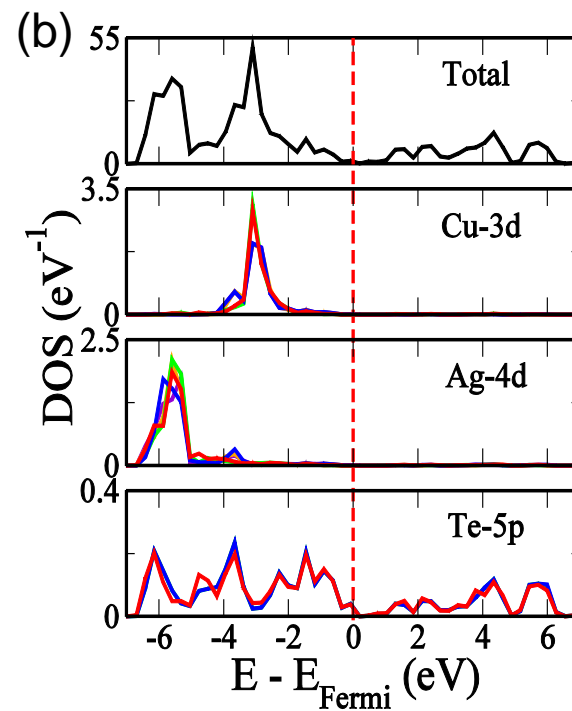


Sample	Carrier Concentration (cm ⁻³)	Mobility (cm ² /Vs)
AgCuTe	9.74×10^{18}	676
AgCuTe _{0.90} Se _{0.10}	6.24×10^{18}	361
AgCuTe _{0.85} Se _{0.15}	4.53×10^{18}	297

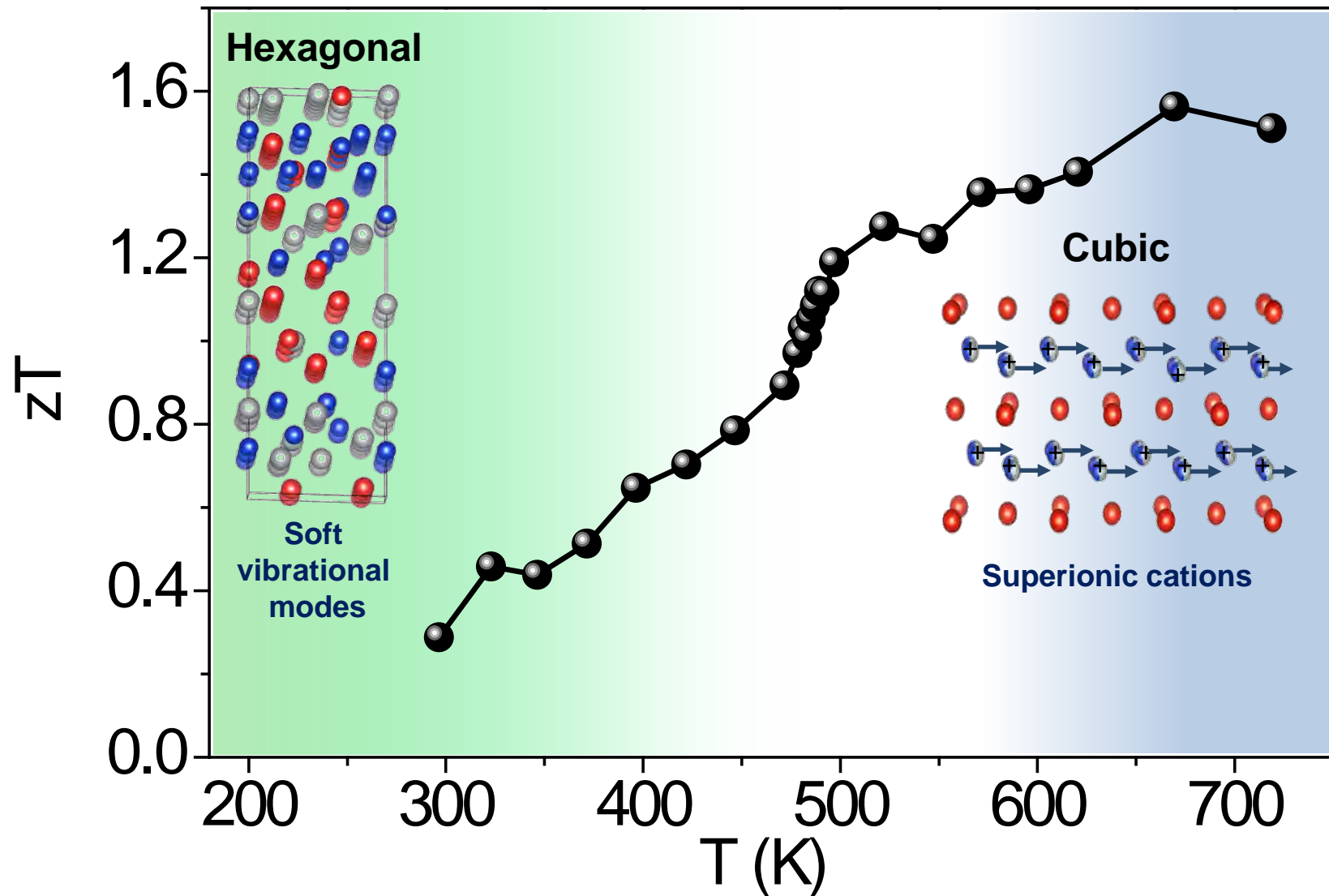
Electronic structure



Hexagonal AgCuTe is semimetallic



Thermoelectric Figure of Merit



Soft Phonon Modes Leading to Ultralow Thermal Conductivity and High Thermoelectric Performance in AgCuTe

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Media Coverage



“JNCASR’s novel material to convert waste heat into electricity”,
(March 03, 2018).



“No side effects: Finding compound that conducts electricity, not heat”,
(March 12, 2018).



“New material raises hope of turning waste heat into power”,
(March 04, 2018).

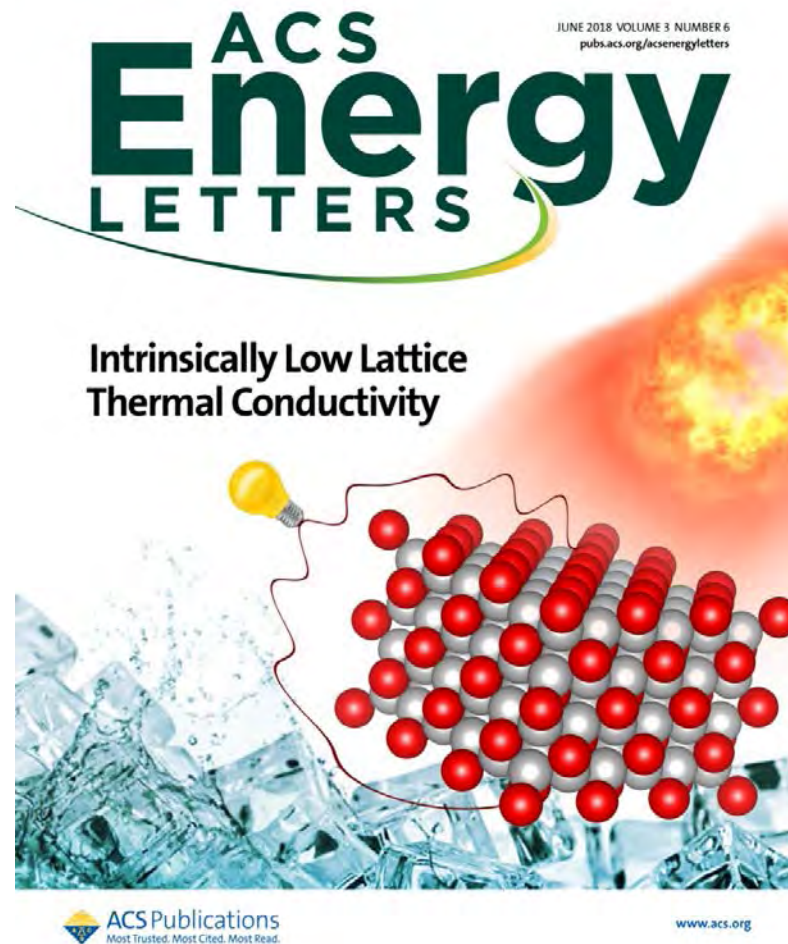


“Can Waste Heat Generate Electricity? These Bengaluru Researchers Say Yes!”,
(March 12, 2018).

DD & Rajya Sabha TV

Conclusions

- Entropy driven extended solid solutions/point defects can scatter phonons heavily, thereby decreases the κ_{lat} .
- Intrinsic low thermal conductivity is an attractive paradigm for developing high performance thermoelectric.
- Bonding hierarchy: Coexistent of rigid covalent substructure with weakly bound ionic substructure resembling the *phonon-glass electron-crystal*.
- Large ADPs and strained lone pair as signatures of low thermal conductivity in search of new thermoelectric materials.
- Soft optical phonons generated by local vibration of selective lattice and complex crystal structure reduce the thermal conductivity.



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